

Please add new claims 73-86.

Sub
H1

E1

--73. A thin film transistor comprising:
a crystalline semiconductor island over a substrate having an insulating surface;
source and drain regions in said semiconductor island;
a channel forming region between said source and drain regions;
a gate insulating film adjacent to at least said channel forming region;
a gate electrode adjacent to said channel forming region having said gate insulating film therebetween,
wherein said channel forming region has no grain boundary, and
wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not higher than $5 \times 10^{18} \text{ cm}^{-3}$, and oxygen at a concentration not higher than $5 \times 10^{19} \text{ cm}^{-3}$.

74. A thin film transistor according to claim 73 wherein said crystalline semiconductor island comprises a material selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au.

75. A thin film transistor according to claim 74 wherein said material is included in said semiconductor island at a concentration not higher than $5 \times 10^{19} \text{ cm}^{-3}$.

Sub H2

76. A thin film transistor according to claim 73 wherein said semiconductor island includes a point defect of $1 \times 10^{16} \text{ cm}^{-3}$ or more, and one of hydrogen and

halogen element for neutralizing the point defect at a concentration of 1×10^{15} to $1 \times 10^{20} \text{ cm}^{-3}$.

Sub
F2

77. A thin film transistor according to claim 73 wherein said semiconductor island includes a spin density of 1×10^{15} to $1 \times 10^{17} \text{ cm}^{-3}$.

78. A thin film transistor according to claim 73 wherein said semiconductor island is a silicon island.

E1
cont.

79. A thin film transistor according to claim 73 wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not lower than $1 \times 10^{16} \text{ cm}^{-3}$, and oxygen at a concentration not lower than $1 \times 10^{17} \text{ cm}^{-3}$.

Sub
F3

80. A thin film transistor comprising:
a crystalline semiconductor island on an insulating surface;
source and drain regions in said semiconductor island;
a channel forming region between said source and drain regions;
a gate insulating film on at least said channel forming region;
a gate electrode over said channel forming region having said gate insulating film therebetween,
wherein said channel forming region has no grain boundary, and
wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not higher than $5 \times 10^{18} \text{ cm}^{-3}$, and oxygen at a concentration not higher than $5 \times 10^{19} \text{ cm}^{-3}$.

81. A thin film transistor according to claim 80 wherein said crystalline semiconductor island comprises a material selected from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, Os, Ir, Pt, Cu, Ag, Au.

82. A thin film transistor according to claim 80 wherein said material is included in said semiconductor island at a concentration not higher than $5 \times 10^{19} \text{ cm}^{-3}$.

83. A thin film transistor according to claim 80 wherein said semiconductor island includes a point defect of $1 \times 10^{16} \text{ cm}^{-3}$ or more, and one of hydrogen and halogen element for neutralizing the point defect at a concentration of 1×10^{15} to $1 \times 10^{20} \text{ cm}^{-3}$.

84. A thin film transistor according to claim 80 wherein said semiconductor island includes a spin density of 1×10^{15} to $1 \times 10^{17} \text{ cm}^{-3}$.

85. A thin film transistor according to claim 80 wherein said semiconductor island is a silicon island.

86. A thin film transistor according to claim 80 wherein said crystalline semiconductor island includes carbon and nitrogen at a concentration not lower than $1 \times 10^{16} \text{ cm}^{-3}$, and oxygen at a concentration not lower than $1 \times 10^{17} \text{ cm}^{-3}$.--